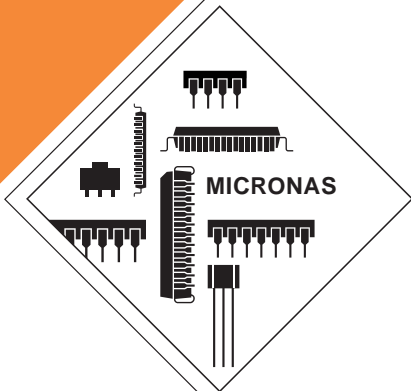


DATA SHEET

# HAL54x Hall Effect Sensor Family



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 MICRONAS

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**Hall Effect Sensor Family**  
in CMOS technology

**1. Introduction**

The HAL54x family consists of different Hall switches produced in CMOS technology. All sensors include a temperature-compensated Hall plate with active offset compensation, a comparator, and an open-drain output transistor. The comparator compares the actual magnetic flux through the Hall plate (Hall voltage) with the fixed reference values (switching points). Accordingly, the output transistor is switched on or off.

In addition to the HAL50x/51x family, the HAL54x features a power-on and undervoltage reset.

The sensors of this family differ in the switching behavior and the switching points.

The active offset compensation leads to constant magnetic characteristics over supply voltage and temperature range. In addition, the magnetic parameters are robust against mechanical stress effects.

The sensors are designed for industrial and automotive applications and operate with supply voltages from 4.3 V to 24 V in the ambient temperature range from -40°C up to 150°C.

All sensors are available in a SMD-package (SOT89B) and in a leaded version (TO-92UA).

**1.1. Features**

- switching offset compensation at typically 62 kHz
- operates from 4.3 V to 24 V supply voltage
- overvoltage protection at all pins
- reverse-voltage protection at V<sub>DD</sub>-pin
- magnetic characteristics are robust against mechanical stress effects
- short-circuit protected open-drain output by thermal shut down
- operates with static magnetic fields and dynamic magnetic fields up to 10 kHz
- constant switching points over a wide supply voltage range
- the decrease of magnetic flux density caused by rising temperature in the sensor system is compensated by a built-in negative temperature coefficient of the magnetic characteristics
- ideal sensor for applications in extreme automotive and industrial environments

**1.2. Family Overview**

The types differ according to the magnetic flux density values for the magnetic switching points and the temperature behavior of the magnetic switching points.

Type	Switching Behavior	Sensitivity	see Page
542	latching	high	14
543	unipolar	low	16
546	unipolar	high	18
548	unipolar	medium	20

**Latching Sensors:**

The output turns low with the magnetic south pole on the branded side of the package and turns high with the magnetic north pole on the branded side. The output does not change if the magnetic field is removed. For changing the output state, the opposite magnetic field polarity must be applied.

**Unipolar Sensors:**

The output turns low with the magnetic south pole on the branded side of the package and turns high if the magnetic field is removed. The sensor does not respond to the magnetic north pole on the branded side.

### 1.3. Marking Code

All Hall sensors have a marking on the package surface (branded side). This marking includes the name of the sensor and the temperature range.

Type	Temperature Range	
	K	E
HAL542	542K	542E
HAL543	543K	543E
HAL546	546K	546E
HAL548	548K	548E

#### 1.3.1. Special Marking of Prototype Parts

Prototype parts are coded with an underscore beneath the temperature range letter on each IC. They may be used for lab experiments and design-ins but are not intended to be used for qualification tests or as production parts.

### 1.4. Operating Junction Temperature Range

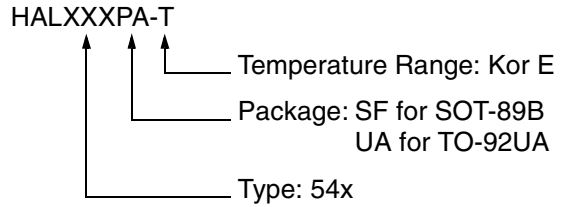
The Hall sensors from Micronas are specified to the chip temperature (junction temperature  $T_J$ ).

**K:**  $T_J = -40\text{ °C to }+140\text{ °C}$

**E:**  $T_J = -40\text{ °C to }+100\text{ °C}$

**Note:** Due to the high power dissipation at high current consumption, there is a difference between the ambient temperature ( $T_A$ ) and junction temperature. Please refer to section 5.1. on page 22 for details.

### 1.5. Hall Sensor Package Codes



Example: **HAL542UA-K**

- Type: 542
- Package: TO-92UA
- Temperature Range:  $T_J = -40\text{ °C to }+140\text{ °C}$

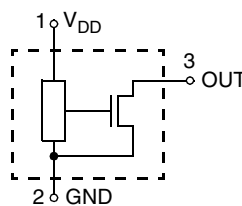
Hall sensors are available in a wide variety of packaging versions and quantities. For more detailed information, please refer to the brochure: "Ordering Codes for Hall Sensors".

### 1.6. Solderability

all packages: according to IEC68-2-58

During soldering reflow processing and manual reworking, a component body temperature of 260 °C should not be exceeded.

Components stored in the original packaging should provide a shelf life of at least 12 months, starting from the date code printed on the labels, even in environments as extreme as 40 °C and 90% relative humidity.



**Fig. 1-1:** Pin configuration

**2. Functional Description**

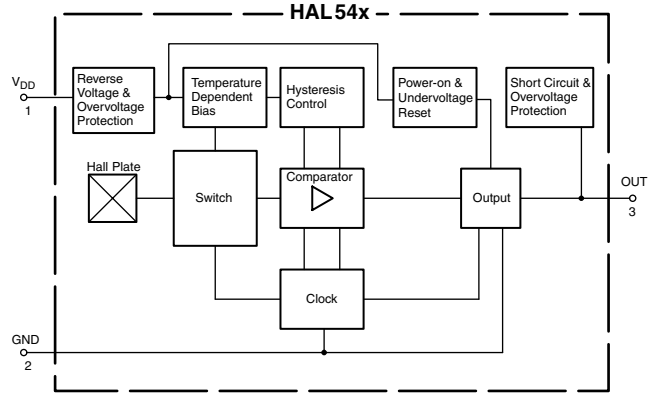
The Hall effect sensor is a monolithic integrated circuit that switches in response to magnetic fields. If a magnetic field with flux lines perpendicular to the sensitive area is applied to the sensor, the biased Hall plate forces a Hall voltage proportional to this field. The Hall voltage is compared with the actual threshold level in the comparator. The temperature-dependent bias increases the supply voltage of the Hall plates and adjusts the switching points to the decreasing induction of magnets at higher temperatures. If the magnetic field exceeds the threshold levels, the open drain output switches to the appropriate state. The built-in hysteresis eliminates oscillation and provides switching behavior of output without bouncing.

Magnetic offset caused by mechanical stress is compensated for by using the “switching offset compensation technique”. Therefore, an internal oscillator provides a two phase clock. The Hall voltage is sampled at the end of the first phase. At the end of the second phase, both sampled and actual Hall voltages are averaged and compared with the actual switching point. Subsequently, the open drain output switches to the appropriate state. The time from crossing the magnetic switching level to switching of output can vary between zero and  $1/f_{osc}$ .

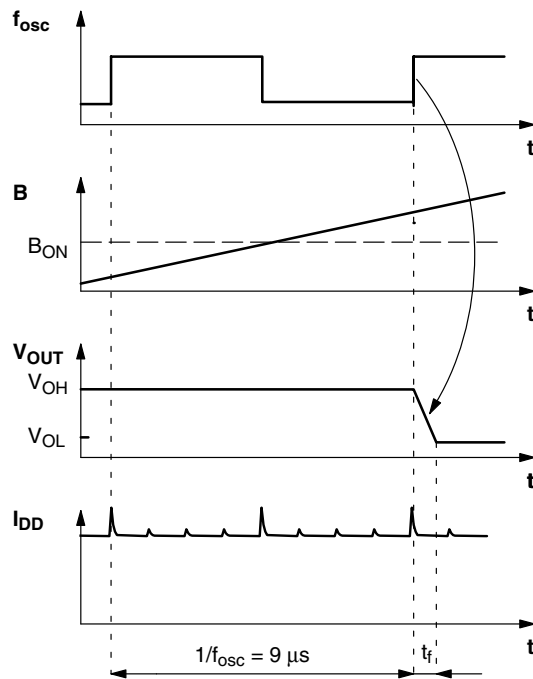
Shunt protection devices clamp voltage peaks at the Output-pin and  $V_{DD}$ -pin together with external series resistors. Reverse current is limited at the  $V_{DD}$ -pin by an internal series resistor up to  $-15$  V. No external reverse protection diode is needed at the  $V_{DD}$ -pin for reverse voltages ranging from  $0$  V to  $-15$  V.

A built-in reset-circuit clamps the output to the “high” state (reset state) during power-on or when the supply voltage drops below a reset voltage of  $V_{reset} < 4.3$  V.

For supply voltages between  $V_{reset}$  and  $4.3$  V, the output state of the device responds to the magnetic field. For supply voltages above  $4.3$  V, the device works according to the specified characteristics.



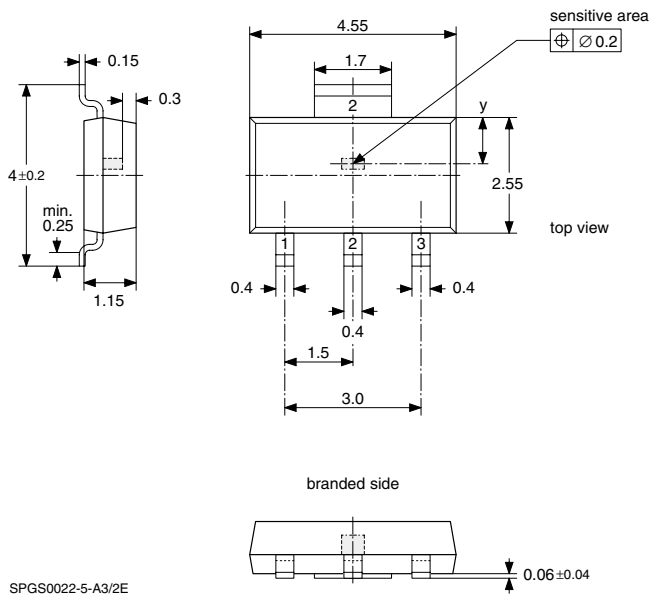
**Fig. 2-1: HAL54x block diagram**



**Fig. 2-2: Timing diagram**

3. Specifications

3.1. Outline Dimensions



SPGS0022-5-A3/2E

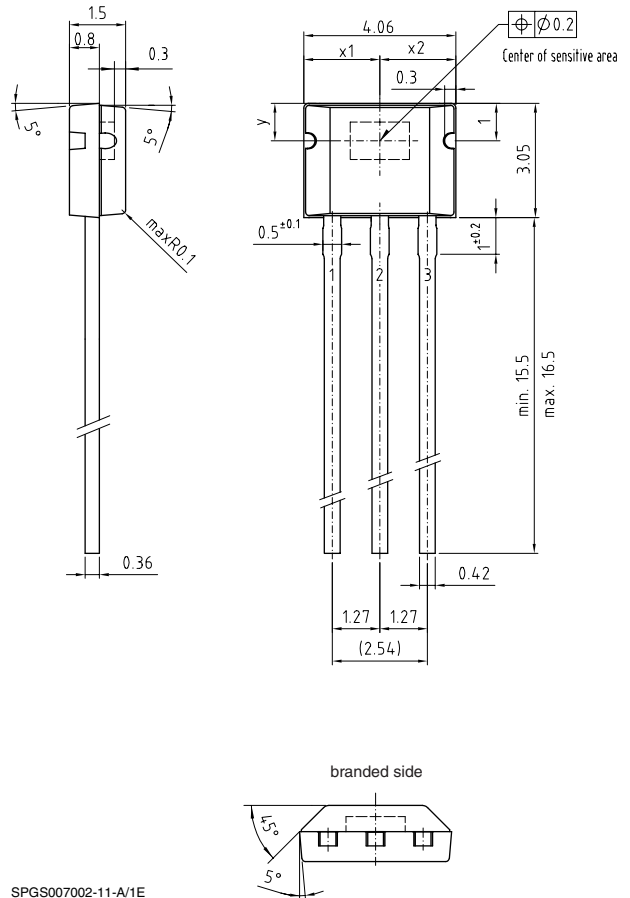
**Fig. 3-1:**  
Plastic Small Outline Transistor Package  
(SOT-89B)  
Weight approximately 0.035 g  
Dimensions in mm

3.2. Dimensions of Sensitive Area

0.25 mm × 0.12 mm

3.3. Positions of Sensitive Areas

	SOT-89B	TO-92UA
x	center of the package	center of the package
y	0.95 mm nominal	1.0 mm nominal



SPGS007002-11-A/1E

**Fig. 3-2:**  
Plastic Transistor Single Outline Package  
(TO-92UA)  
Weight approximately 0.12 g  
Dimensions in mm

**Note:** For all package diagrams, a mechanical tolerance of  $\pm 0.05$  mm applies to all dimensions where no tolerance is explicitly given. Package dimensions exclude moulding flash.

### 3.4. Absolute Maximum Ratings

Symbol	Parameter	Pin Name	Min.	Max.	Unit
V <sub>DD</sub>	Supply Voltage	1	-15	28 <sup>1)</sup>	V
V <sub>O</sub>	Output Voltage	3	-0.3	28 <sup>1)</sup>	V
I <sub>O</sub>	Continuous Output On Current	3	-	50 <sup>1)</sup>	mA
T <sub>J</sub>	Junction Temperature Range		-40	170	°C
1) as long as T <sub>Jmax</sub> is not exceeded					

Stresses beyond those listed in the “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only. Functional operation of the device at these or any other conditions beyond those indicated in the “Recommended Operating Conditions/Characteristics” of this specification is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

#### 3.4.1. Storage, Moisture Sensitivity Class, and Shelf Life

Storage has no influence on the electrical and magnetic characteristics of the sensors. However, under disadvantageous conditions, extended storage time can lead to alteration of the lead plating, which affects the soldering process.

Moisture Sensitivity Class: The package SOT-89B achieves level 1 according to J-STD-020A “Moisture/ Reflow Sensitivity Classification for Non-hermetic Solid State Surface Mount Devices”. If the sensors are stored at a maximum 30 °C and a maximum 90% relative humidity, no Dry Pack is required.

The permissible storage time (shelf life) of the sensors is a minimum of 12 months, starting from the date of manufacture, if they are stored in the original packaging at a maximum of 40 °C ambient temperature and a maximum of 90% relative humidity.

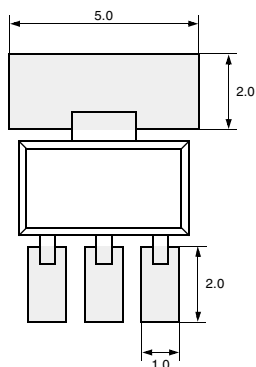
### 3.5. Recommended Operating Conditions

Symbol	Parameter	Pin Name	Min.	Max.	Unit
V <sub>DD</sub>	Supply Voltage	1	4.3	24	V
I <sub>O</sub>	Continuous Output On Current	3	0	20	mA
V <sub>O</sub>	Output Voltage (output switched off)	3	0	24	V

**3.6. Electrical Characteristics** at  $T_J = -40\text{ }^\circ\text{C}$  to  $+140\text{ }^\circ\text{C}$ ,  $V_{DD} = 4.3\text{ V}$  to  $24\text{ V}$ , as not otherwise specified in Conditions.  
 Typical Characteristics for  $T_J = 25\text{ }^\circ\text{C}$  and  $V_{DD} = 12\text{ V}$

Symbol	Parameter	Pin No.	Min.	Typ.	Max.	Unit	Conditions
$I_{DD}$	Supply Current	1	2.3	3	4.2	mA	$T_J = 25\text{ }^\circ\text{C}$
$I_{DD}$	Supply Current over Temperature Range	1	1.6	3	5.2	mA	
$V_{DDZ}$	Overshoot Protection at Supply	1	-	28.5	32	V	$I_{DD} = 25\text{ mA}$ , $T_J = 25\text{ }^\circ\text{C}$ , $t = 20\text{ ms}$
$V_{OZ}$	Overshoot Protection at Output	3	-	28	32	V	$I_{OH} = 25\text{ mA}$ , $T_J = 25\text{ }^\circ\text{C}$ , $t = 20\text{ ms}$
$V_{OL}$	Output Voltage	3	-	130	280	mV	$I_{OL} = 20\text{ mA}$ , $T_J = 25\text{ }^\circ\text{C}$
$V_{OL}$	Output Voltage over Temperature Range	3	-	130	400	mV	$I_{OL} = 20\text{ mA}$
$I_{OH}$	Output Leakage Current	3	-	0.06	0.1	$\mu\text{A}$	Output switched off, $T_J = 25\text{ }^\circ\text{C}$ , $V_{OH} = 4.3\text{ to }24\text{ V}$
$I_{OH}$	Output Leakage Current over Temperature Range	3	-	-	10	$\mu\text{A}$	Output switched off, $T_J \leq 150\text{ }^\circ\text{C}$ , $V_{OH} = 4.3\text{ to }24\text{ V}$
$f_{osc}$	Internal Oscillator Chopper Frequency	-	-	62	-	kHz	$T_J = 25\text{ }^\circ\text{C}$ , $V_{DD} = 4.5\text{ to }24\text{ V}$
$V_{reset}$	Reset Voltage	1	-	3.8	-	V	
$t_{en(O)}$	Enable Time of Output after Setting of $V_{DD}$	1	-	70	-	$\mu\text{s}$	$V_{DD} = 12\text{ V}^{2)}$
$t_r$	Output Rise Time	3	-	75	400	ns	$V_{DD} = 12\text{ V}$ , $R_L = 820\text{ Ohm}$ , $C_L = 20\text{ pF}$
$t_f$	Output Fall Time	3	-	50	400	ns	
$R_{thJSB}$ case SOT-89B	Thermal Resistance Junction to Substrate Backside	-	-	150	200	K/W	Fiberglass Substrate 30 mm x 10 mm x 1.5 mm, pad size (see Fig. 3-3)
$R_{thJA}$ case TO-92UA	Thermal Resistance Junction to Soldering Point	-	-	150	200	K/W	

<sup>2)</sup>  $B > B_{ON} + 2\text{ mT}$  or  $B < B_{OFF} - 2\text{ mT}$



**Fig. 3-3:** Recommended pad size SOT-89B  
 Dimensions in mm



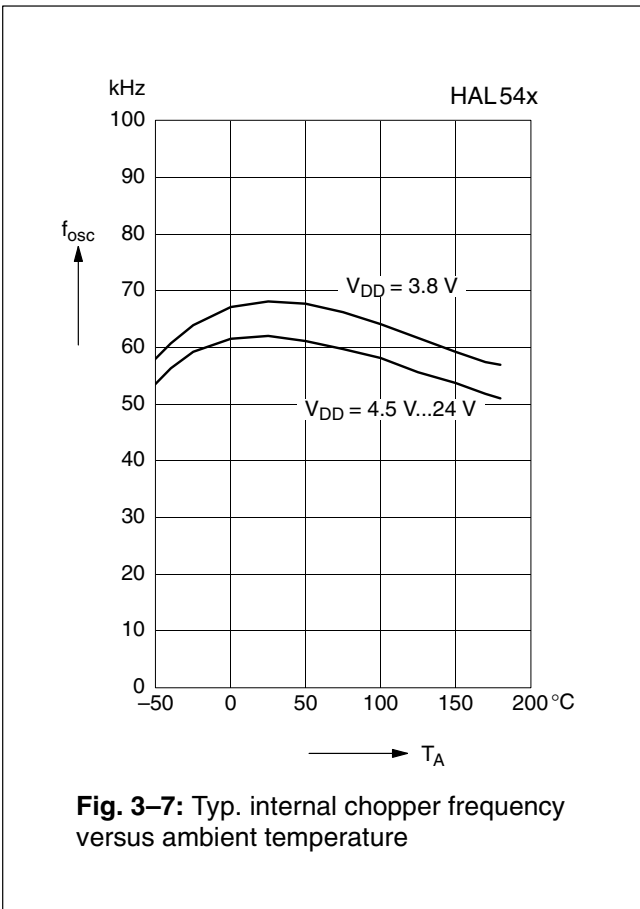
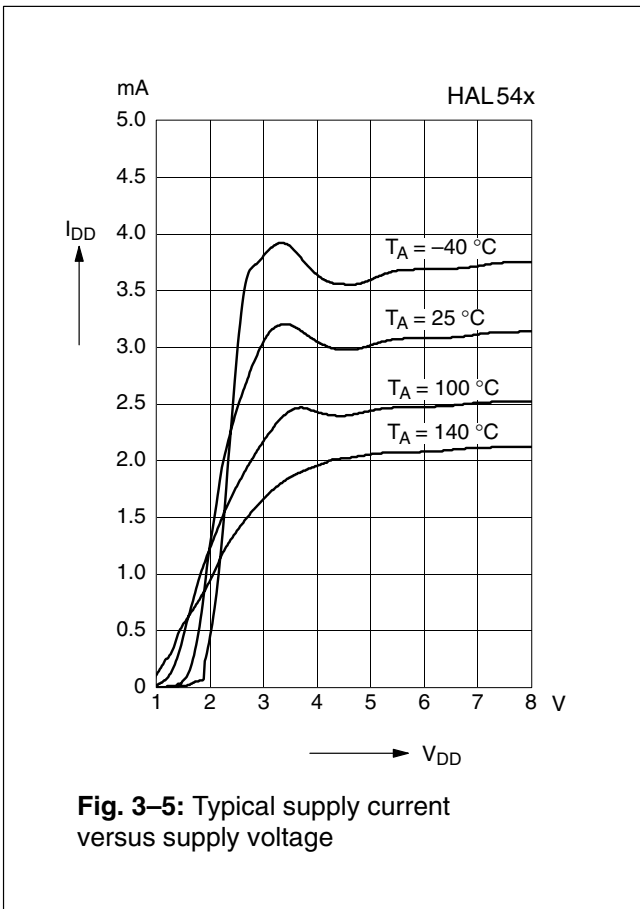
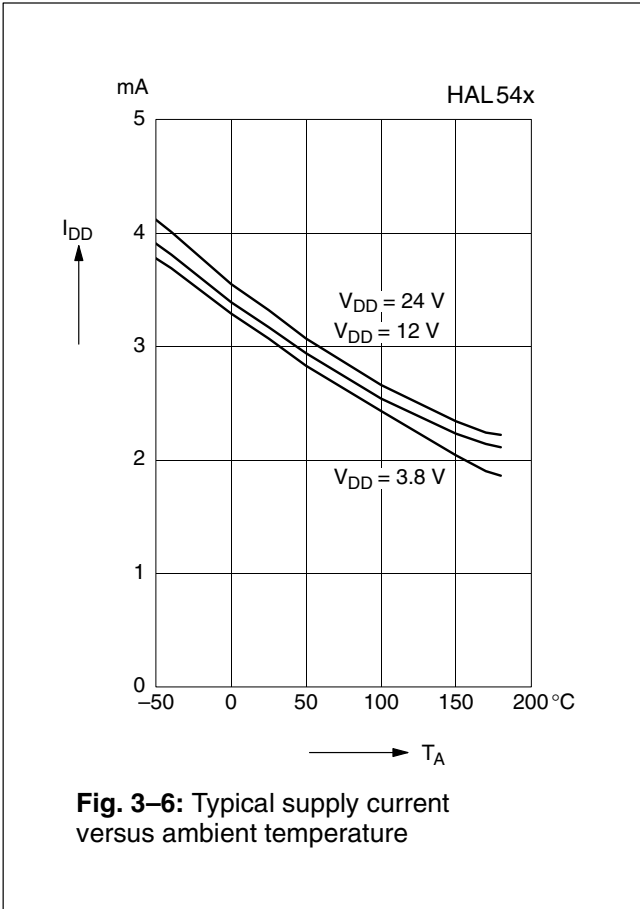
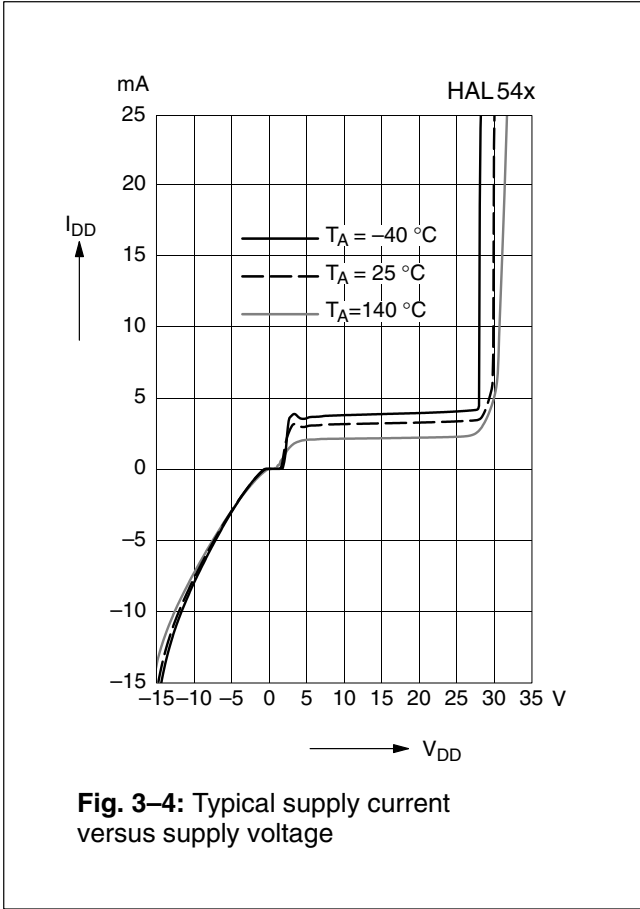
**3.7. Magnetic Characteristics Overview** at  $T_J = -40\text{ °C}$  to  $+140\text{ °C}$ ,  $V_{DD} = 4.3\text{ V}$  to  $24\text{ V}$ ,  
Typical Characteristics for  $V_{DD} = 12\text{ V}$

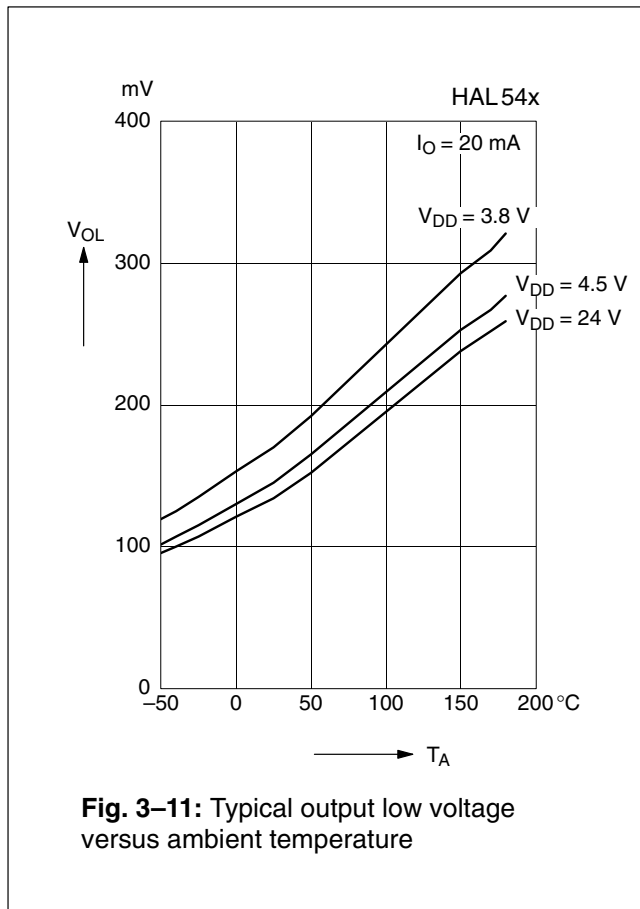
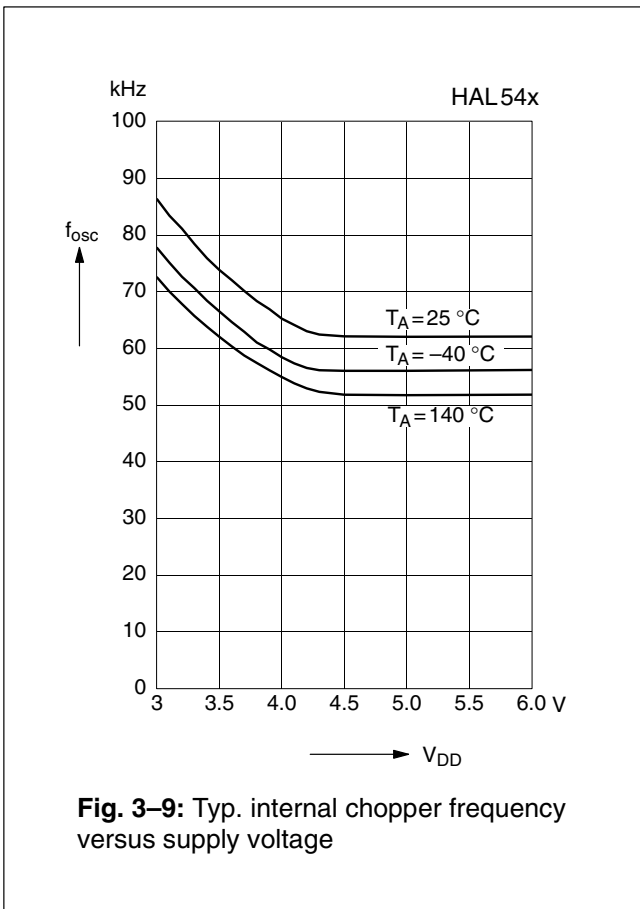
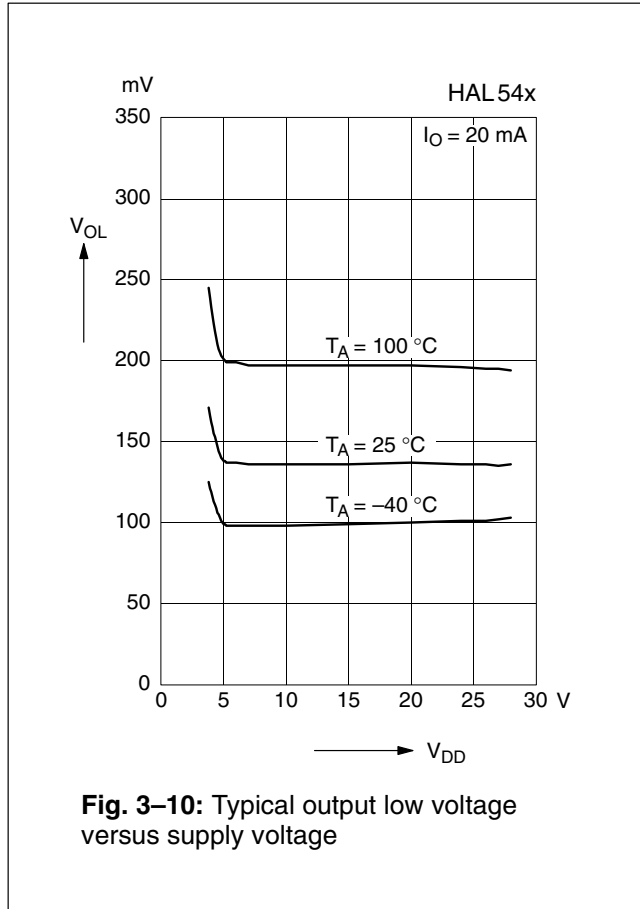
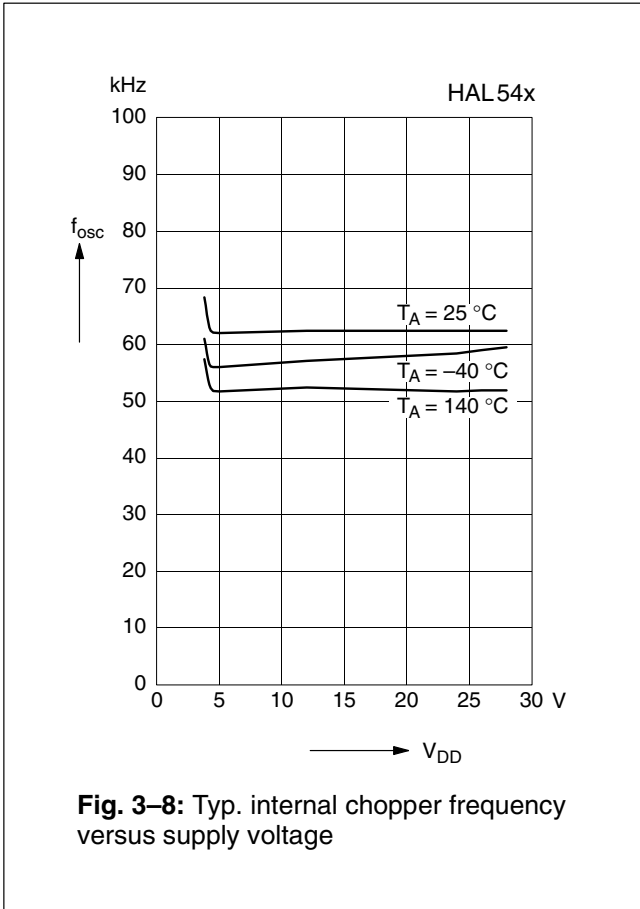
Magnetic flux density values of switching points.

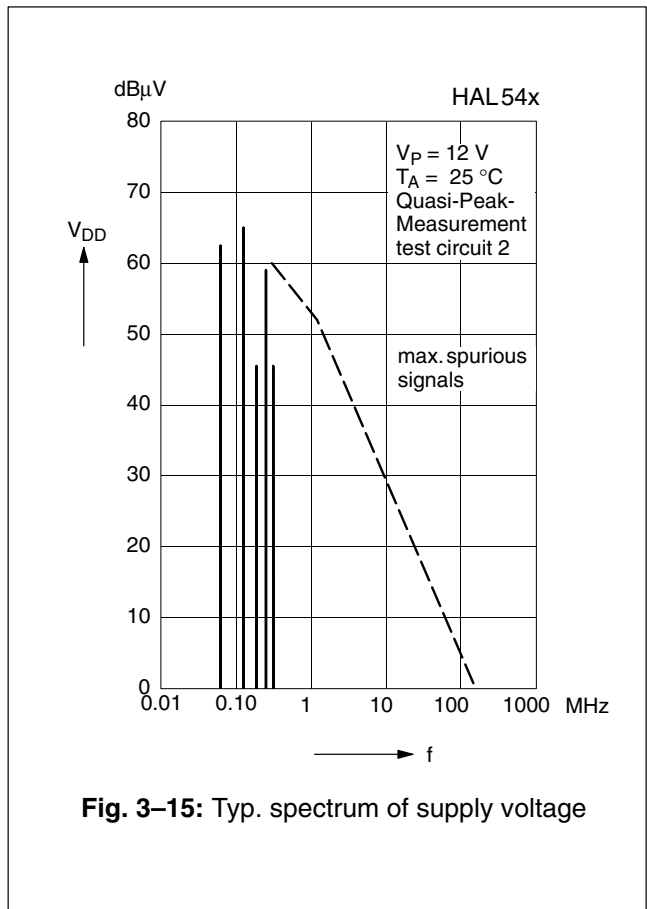
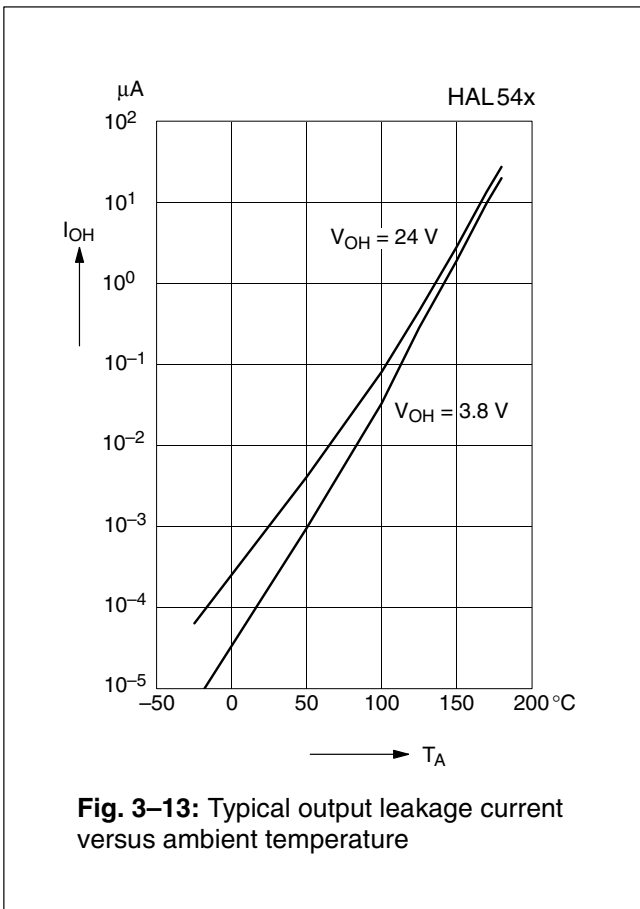
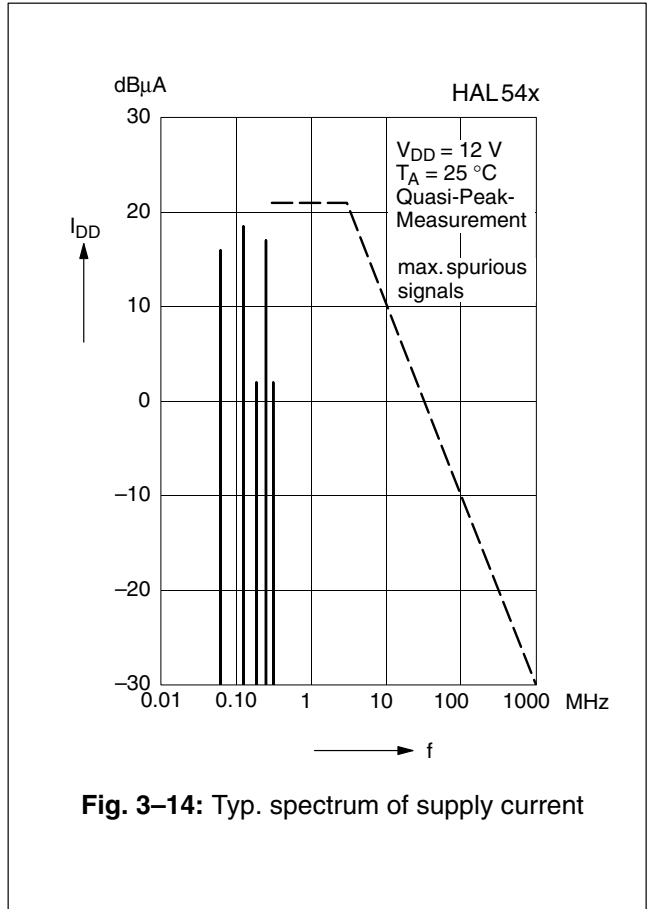
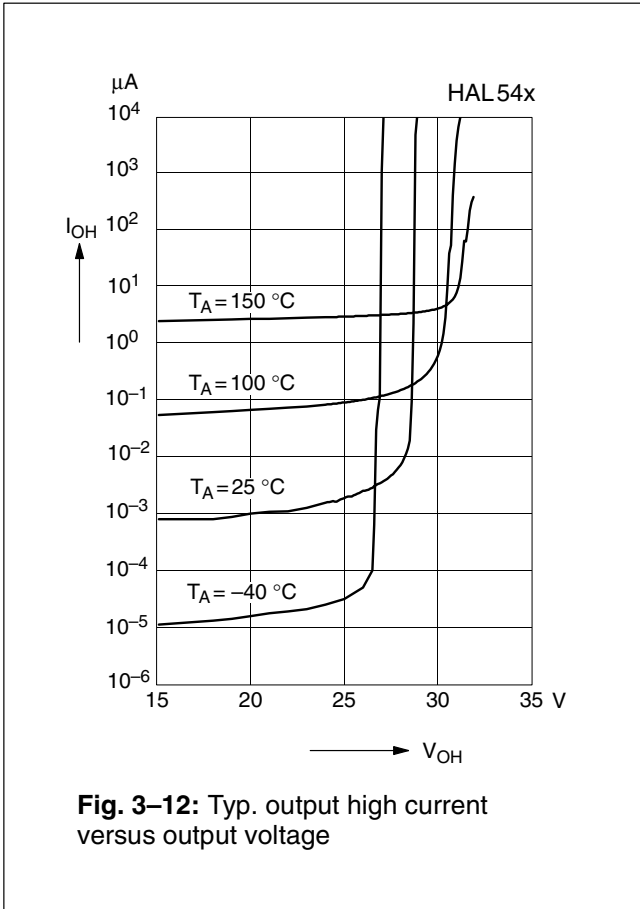
Positive flux density values refer to the magnetic south pole at the branded side of the package.

Sensor Switching Type	Parameter $T_J$	On point $B_{ON}$			Off point $B_{OFF}$			Hysteresis $B_{HYS}$			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
HAL542 latching	-40 °C	1	2.8	5	-5	-2.8	-1	4.5	5.85	7.2	mT
	25 °C	1	2.6	4.5	-4.5	-2.6	-1	4.5	5.5	6.5	mT
	140 °C	0.5	2.3	4.8	-4.8	-2.3	-0.5	3.0	4.0	6.0	mT
HAL543 unipolar	-40 °C	21	27	33	15	21	27	4	6	8	mT
	25 °C	21	27	33	15	21	27	4	6	8	mT
	140 °C	21	26	33	15	20	27	4	5.5	8	mT
HAL546 unipolar	-40 °C	4.3	5.9	7.7	2.1	3.8	5.5	1.5	2.1	2.9	mT
	25 °C	3.8	5.5	7.2	2	3.5	5	1.4	2	2.8	mT
	140 °C	3.2	4.8	6.9	1.8	3.1	5.5	1	1.7	2.6	mT
HAL548 unipolar	-40 °C	12	19	24	6	13	18	4	6.2	8	mT
	25 °C	12	18	24	6	12	18	4	5.6	8	mT
	140 °C	12	16	24	6	11	18	4	5	8	mT

**Note:** For detailed descriptions of the individual types, see pages 14 and following.







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**4. Type Descriptions**

**4.1. HAL542**

The HAL542 is the most sensitive latching sensor of this family (see Fig. 4–1).

The output turns low with the magnetic south pole on the branded side of the package and turns high with the magnetic north pole on the branded side. The output does not change if the magnetic field is removed. For changing the output state, the opposite magnetic field polarity must be applied.

For correct functioning in the application, the sensor requires both magnetic polarities (north and south) on the branded side of the package.

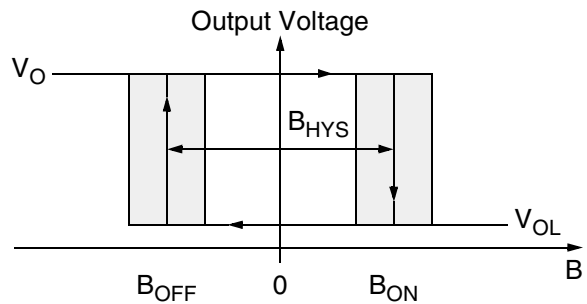
**Magnetic Features:**

- switching type: latching
- high sensitivity
- typical  $B_{ON}$ : 2.6 mT at room temperature
- typical  $B_{OFF}$ : -2.6 mT at room temperature
- operates with static magnetic fields and dynamic magnetic fields up to 10 kHz
- typical temperature coefficient of magnetic switching points is -1000 ppm/K

**Applications**

The HAL542 is the optimal sensor for applications with alternating magnetic signals and weak magnetic amplitude at the sensor position such as:

- applications with large airgap or weak magnets,
- rotating speed measurement,
- commutation of brushless DC motors, and
- CAM shaft sensors, and
- magnetic encoders.



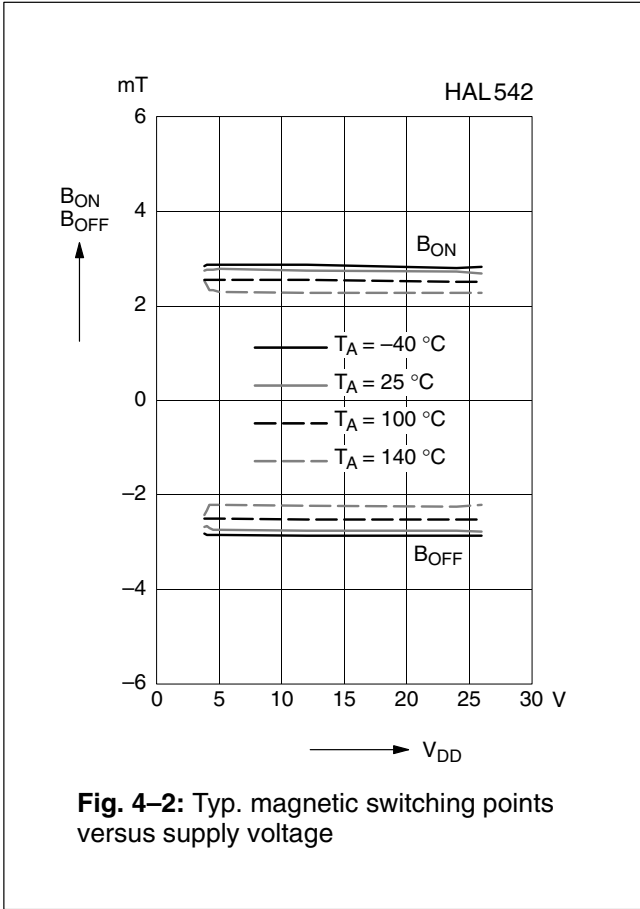
**Fig. 4–1:** Definition of magnetic switching points for the HAL542

**Magnetic Characteristics** at  $T_J = -40\text{ °C}$  to  $+140\text{ °C}$ ,  $V_{DD} = 4.3\text{ V}$  to  $24\text{ V}$ , Typical Characteristics for  $V_{DD} = 12\text{ V}$

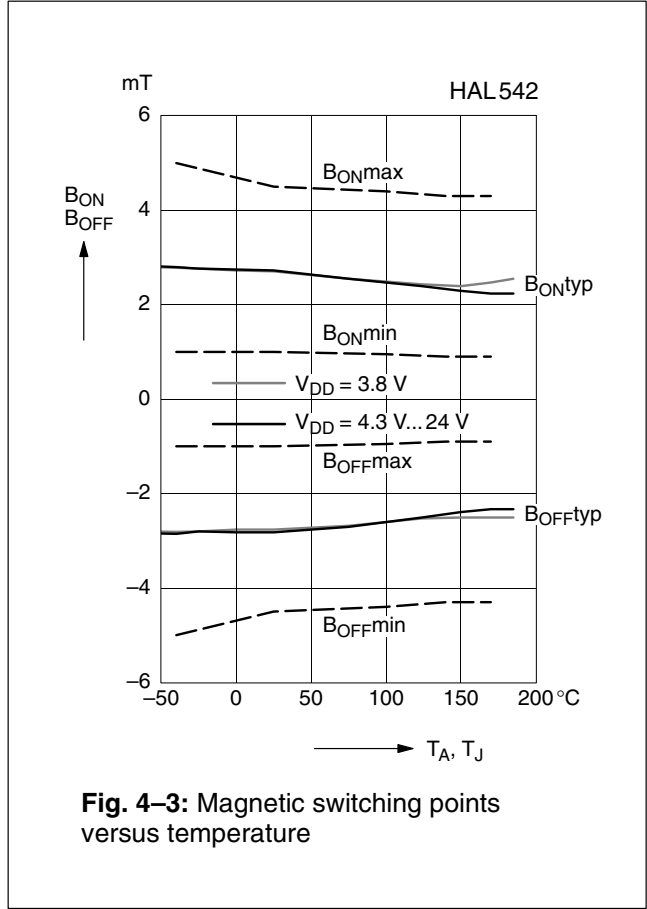
Magnetic flux density values of switching points. Positive flux density values refer to the magnetic south pole at the branded side of the package.

Parameter	On point $B_{ON}$			Off point $B_{OFF}$			Hysteresis $B_{HYS}$			Magnetic Offset			Unit
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
$T_J$													
-40 °C	1	2.8	5	-5	-2.8	-1	4.5	5.85	7.2		0		mT
25 °C	1	2.6	4.5	-4.5	-2.6	-1	4.5	5.5	6.5	-1.5	0	1.5	mT
100 °C	0.95	2.5	4.4	-4.4	-2.5	-0.95	3.7	5.0	6.3		0		mT
140 °C	0.6	2.4	4.6	-4.6	-2.4	-0.6	3.3	4.8	6.2		0		mT

The hysteresis is the difference between the switching points  $B_{HYS} = B_{ON} - B_{OFF}$   
 The magnetic offset is the mean value of the switching points  $B_{OFFSET} = (B_{ON} + B_{OFF}) / 2$



**Fig. 4-2:** Typ. magnetic switching points versus supply voltage



**Fig. 4-3:** Magnetic switching points versus temperature

**Note:** In the diagram “Magnetic switching points versus ambient temperature”, the curves for  $B_{ONmin}$ ,  $B_{ONmax}$ ,  $B_{OFFmin}$ , and  $B_{OFFmax}$  refer to junction temperature, whereas typical curves refer to ambient temperature.

**4.2. HAL543**

The HAL543 is the most insensitive unipolar sensor of this family (see Fig. 4–4).

The output turns low with the magnetic south pole on the branded side of the package and turns high if the magnetic field is removed. The sensor does not respond to the magnetic north pole on the branded side.

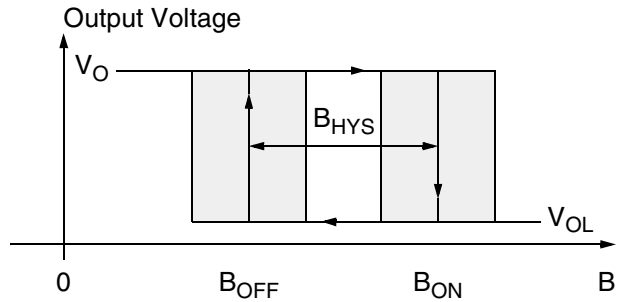
**Magnetic Features:**

- switching type: unipolar
- low sensitivity
- typical  $B_{ON}$ : 27 mT at room temperature
- typical  $B_{OFF}$ : 21 mT at room temperature
- operates with static magnetic fields and dynamic magnetic fields up to 10 kHz

**Applications**

The HAL543 is the optimal sensor for applications with unipolar magnetic signals and large magnetic amplitude at the sensor position such as:

- position and end point detection,
- contactless solution to replace micro switches,
- rotating speed measurement.



**Fig. 4–4:** Definition of magnetic switching points for the HAL543

**Magnetic Characteristics** at  $T_J = -40\text{ °C}$  to  $+140\text{ °C}$ ,  $V_{DD} = 4.3\text{ V}$  to  $24\text{ V}$ , Typical Characteristics for  $V_{DD} = 12\text{ V}$

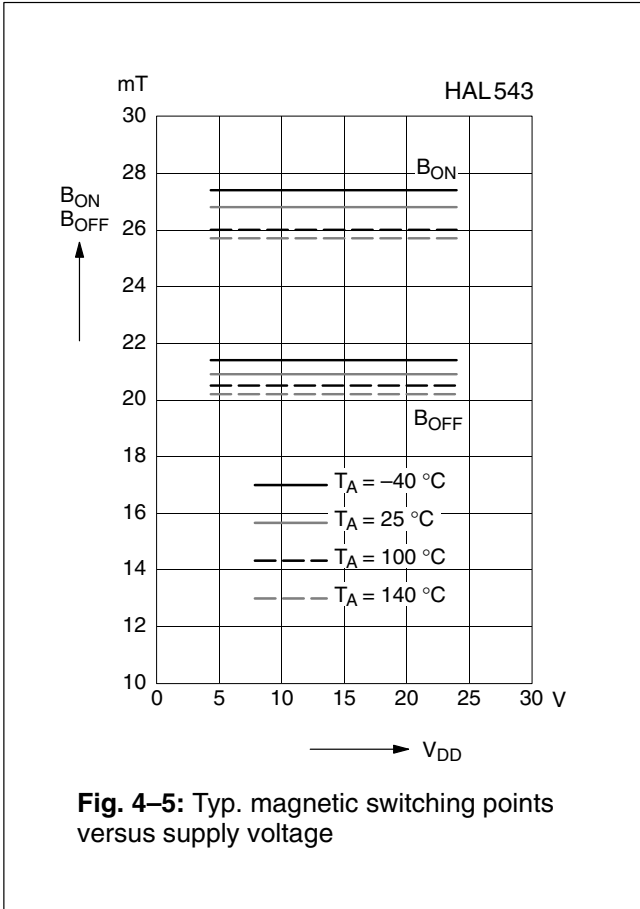
Magnetic flux density values of switching points.

Positive flux density values refer to the magnetic south pole at the branded side of the package.

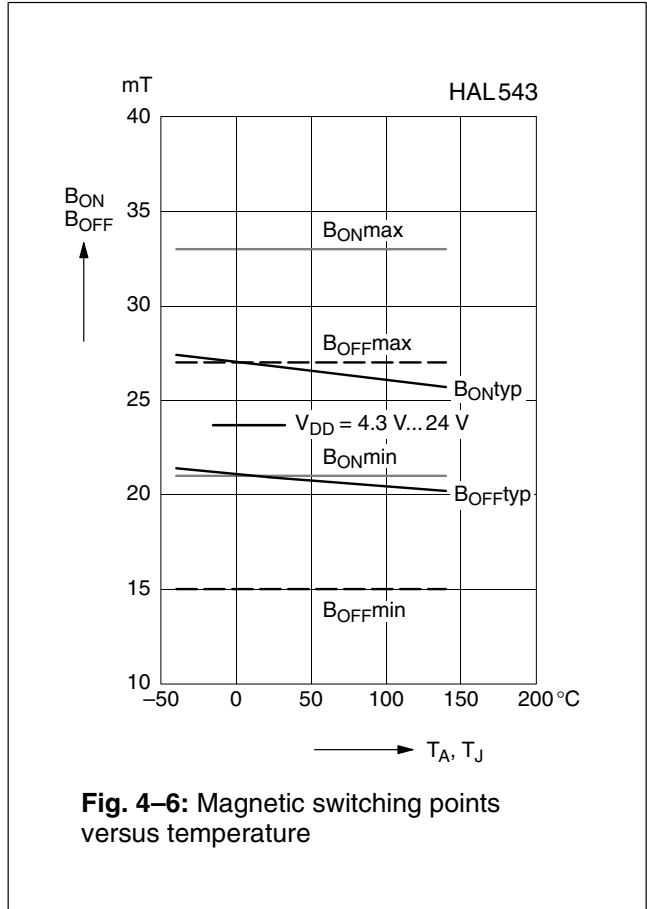
Parameter $T_J$	On point $B_{ON}$			Off point $B_{OFF}$			Hysteresis $B_{HYS}$			Magnetic Offset			Unit
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
-40 °C	21	27	33	15	21	27	4	6	8	–	24	–	mT
25 °C	21	27	33	15	21	27	4	6	8	18	24	30	mT
100 °C	21	27	33	15	21	27	4	6	8	–	24	–	mT
140 °C	21	27	33	15	21	27	4	5.5	8	–	24	–	mT

The hysteresis is the difference between the switching points  $B_{HYS} = B_{ON} - B_{OFF}$   
 The magnetic offset is the mean value of the switching points  $B_{OFFSET} = (B_{ON} + B_{OFF}) / 2$





**Fig. 4-5:** Typ. magnetic switching points versus supply voltage



**Fig. 4-6:** Magnetic switching points versus temperature

**Note:** In the diagram “Magnetic switching points versus ambient temperature”, the curves for  $B_{ONmin}$ ,  $B_{ONmax}$ ,  $B_{OFFmin}$ , and  $B_{OFFmax}$  refer to junction temperature, whereas typical curves refer to ambient temperature.

**4.3. HAL546**

The HAL546 is a quite sensitive unipolar sensor (see Fig. 4–7).

The output turns low with the magnetic south pole on the branded side of the package and turns high if the magnetic field is removed. The sensor does not respond to the magnetic north pole on the branded side.

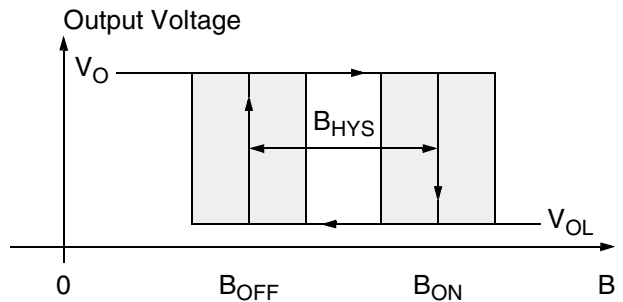
**Magnetic Features:**

- switching type: unipolar
- high sensitivity
- typical  $B_{ON}$ : 5.5 mT at room temperature
- typical  $B_{OFF}$ : 3.5 mT at room temperature
- operates with static magnetic fields and dynamic magnetic fields up to 10 kHz
- typical temperature coefficient of magnetic switching points is  $-1000$  ppm/K.

**Applications**

The HAL546 is the optimal sensor for applications with one magnetic polarity such as:

- solid state switches,
- contactless solution to replace micro-switches, and
- rotating speed measurement.



**Fig. 4–7:** Definition of magnetic switching points for the HAL546

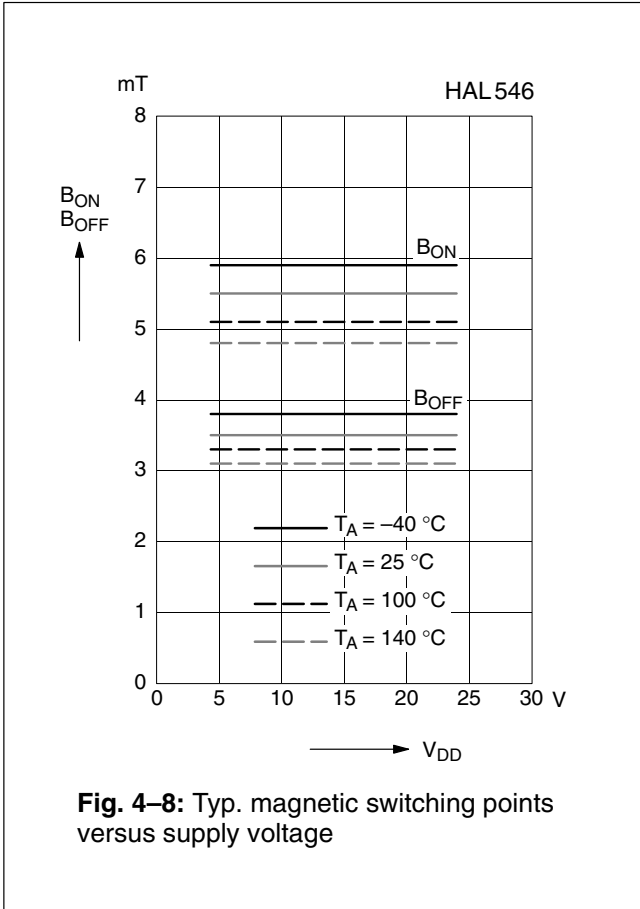
**Magnetic Characteristics** at  $T_J = -40$  °C to  $+140$  °C,  $V_{DD} = 4.3$  V to 24 V, Typical Characteristics for  $V_{DD} = 12$  V

Magnetic flux density values of switching points.

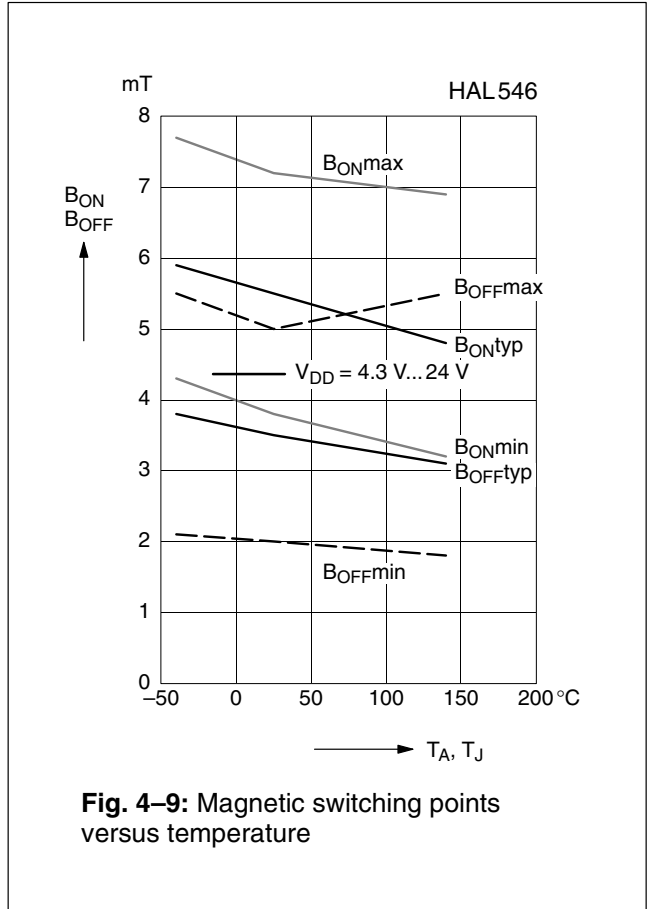
Positive flux density values refer to the magnetic south pole at the branded side of the package.

Parameter $T_J$	On point $B_{ON}$			Off point $B_{OFF}$			Hysteresis $B_{HYS}$			Magnetic Offset			Unit
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
-40 °C	4.3	5.9	7.7	2.1	3.8	5.5	1.5	2.1	2.9	–	4.9	–	mT
25 °C	3.8	5.5	7.2	2	3.5	5	1.4	2	2.8	2.9	4.5	6.1	mT
100 °C	3.5	5.3	7	1.9	3.3	5.4	1.1	1.9	2.6	–	4.3	–	mT
140 °C	3.2	4.8	6.9	1.8	3.1	5.5	1	1.7	2.6	–	4	–	mT

The hysteresis is the difference between the switching points  $B_{HYS} = B_{ON} - B_{OFF}$   
 The magnetic offset is the mean value of the switching points  $B_{OFFSET} = (B_{ON} + B_{OFF}) / 2$



**Fig. 4-8:** Typ. magnetic switching points versus supply voltage



**Fig. 4-9:** Magnetic switching points versus temperature

**Note:** In the diagram “Magnetic switching points versus ambient temperature”, the curves for  $B_{ONmin}$ ,  $B_{ONmax}$ ,  $B_{OFFmin}$ , and  $B_{OFFmax}$  refer to junction temperature, whereas typical curves refer to ambient temperature.

**4.4. HAL548**

The HAL548 is a unipolar switching sensor (see Fig. 4–10).

The output turns low with the magnetic south pole on the branded side of the package and turns high if the magnetic field is removed. The sensor does not respond to the magnetic north pole on the branded side.

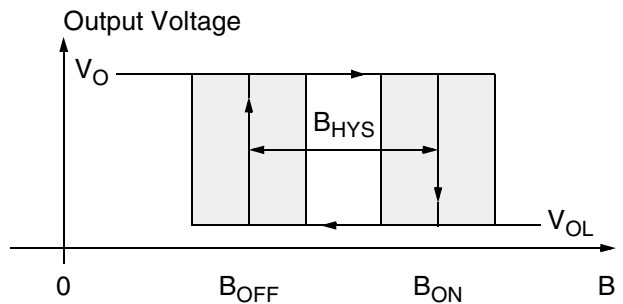
**Magnetic Features:**

- switching type: unipolar,
- medium sensitivity
- typical  $B_{ON}$ : 18 mT at room temperature
- typical  $B_{OFF}$ : 12 mT at room temperature
- operates with static magnetic fields and dynamic magnetic fields up to 10 kHz

**Applications**

The HAL548 is the ideal sensor for all applications with one magnetic polarity and weak magnetic amplitude at the sensor position such as:

- solid state switches,
- contactless solution to replace micro switches,
- position and end point detection, and
- rotating speed measurement.



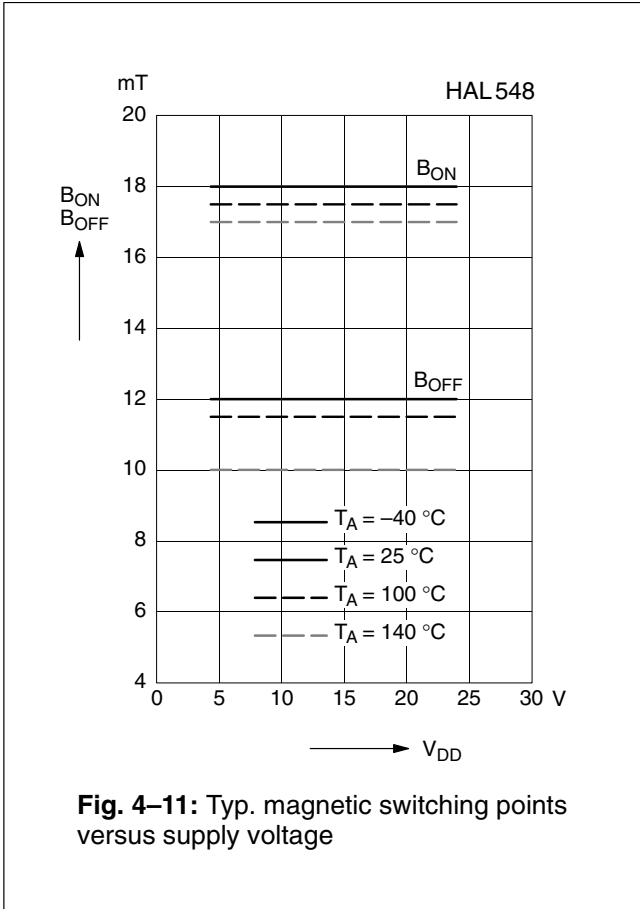
**Fig. 4–10:** Definition of magnetic switching points for the HAL548

**Magnetic Characteristics** at  $T_J = -40\text{ °C}$  to  $+140\text{ °C}$ ,  $V_{DD} = 4.3\text{ V}$  to  $24\text{ V}$ , Typical Characteristics for  $V_{DD} = 12\text{ V}$

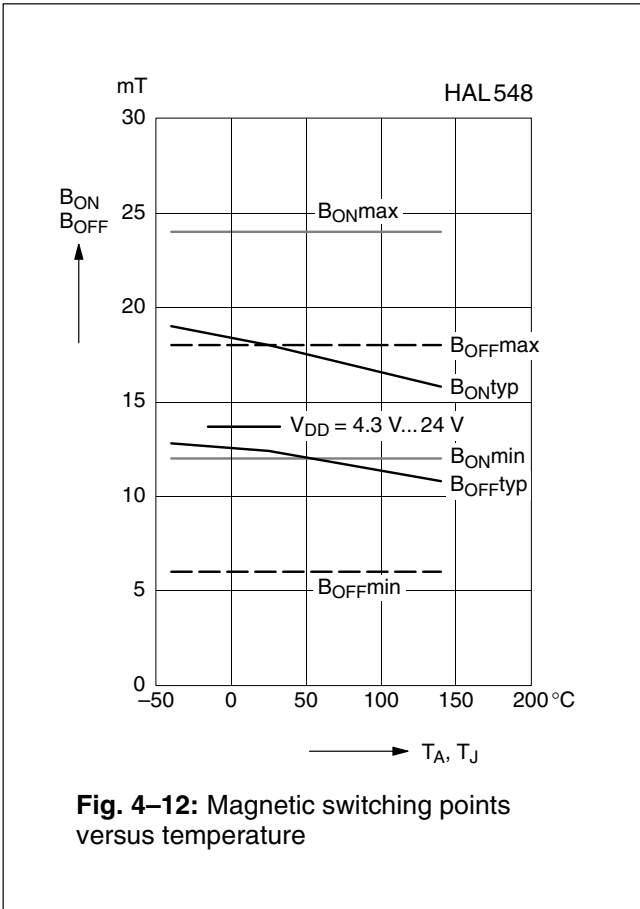
Magnetic flux density values of switching points. Positive flux density values refer to the magnetic south pole at the branded side of the package.

Parameter $T_J$	On point $B_{ON}$			Off point $B_{OFF}$			Hysteresis $B_{HYS}$			Magnetic Offset			Unit
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
-40 °C	12	19	24	6	13	18	4	6	8	–	16	–	mT
25 °C	12	18	24	6	12	18	4	6	8	9	15	21	mT
100 °C	12	18	24	6	12	18	4	6	8	–	15	–	mT
140 °C	12	17	24	6	11	18	4	6	8	–	14	–	mT

The hysteresis is the difference between the switching points  $B_{HYS} = B_{ON} - B_{OFF}$   
 The magnetic offset is the mean value of the switching points  $B_{OFFSET} = (B_{ON} + B_{OFF}) / 2$



**Fig. 4-11:** Typ. magnetic switching points versus supply voltage



**Fig. 4-12:** Magnetic switching points versus temperature

**Note:** In the diagram “Magnetic switching points versus ambient temperature”, the curves for  $B_{ONmin}$ ,  $B_{ONmax}$ ,  $B_{OFFmin}$ , and  $B_{OFFmax}$  refer to junction temperature, whereas typical curves refer to ambient temperature.

**5. Application**

**5.1. Ambient Temperature**

Due to the internal power dissipation, the temperature on the silicon chip (junction temperature  $T_J$ ) is higher than the temperature outside the package (ambient temperature  $T_A$ ).

$$T_J = T_A + \Delta T$$

Under static conditions and continuous operation, the following equation applies:

$$\Delta T = I_{DD} * V_{DD} * R_{th}$$

For typical values, use the typical parameters. For worst case calculation, use the max. parameters for  $I_{DD}$  and  $R_{th}$ , and the max. value for  $V_{DD}$  from the application.

For all sensors, the junction temperature range  $T_J$  is specified. The maximum ambient temperature  $T_{Amax}$  can be calculated as:

$$T_{Amax} = T_{Jmax} - \Delta T$$

**5.2. Extended Operating Conditions**

All sensors fulfill the electrical and magnetic characteristics when operated within the Recommended Operating Conditions (see page 8).

**Supply Voltage Below 4.3 V**

The devices contain a Power-on Reset (POR) and a undervoltage reset. For  $V_{dd} < V_{reset}$  the output state is high. For  $V_{reset} < V_{dd} < 4.3$  V the device responds to the magnetic field according to the specified magnetic characteristics.

**5.3. Start-up Behavior**

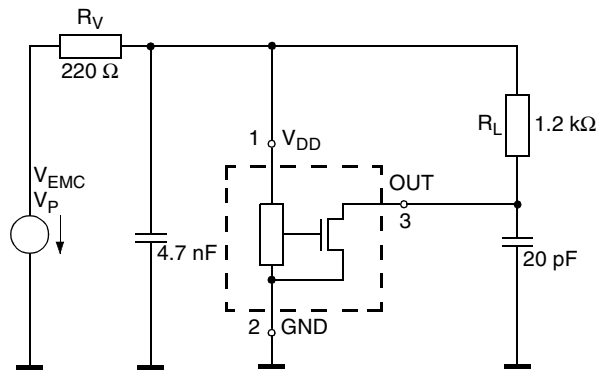
Due to the active offset compensation, the sensors have an initialization time (enable time  $t_{en(O)}$ ) after applying the supply voltage. The parameter  $t_{en(O)}$  is specified in the Electrical Characteristics (see page 9).

During the initialization time, the output state for the HAL54x is 'Off-state' (i.e. Output High). After  $t_{en(O)}$ , the output will be high. The output will be switched to low if the applied magnetic field  $B$  is above  $B_{ON}$ .

**5.4. EMC and ESD**

For applications with disturbances on the supply line or radiated disturbances, a series resistor and a capacitor are recommended (see Fig. 5–1). The series resistor and the capacitor should be placed as closely as possible to the Hall sensor.

Please contact Micronas for the detailed investigation reports with the EMC and ESD results.



**Fig. 5–1:** Test circuit for EMC investigations

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**WARNING:**  
DO NOT USE THESE SENSORS IN LIFE-SUPPORTING SYSTEMS, AVIATION, AND AEROSPACE APPLICATIONS.

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**6. Data Sheet History**

1. Data Sheet: "HAL54x Hall Effect Sensor Family", Nov. 27, 2002, 6251-605-1DS. First release of the data sheet.

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